



2SB1201/2SD1801

High-Current Switching Applications

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment.

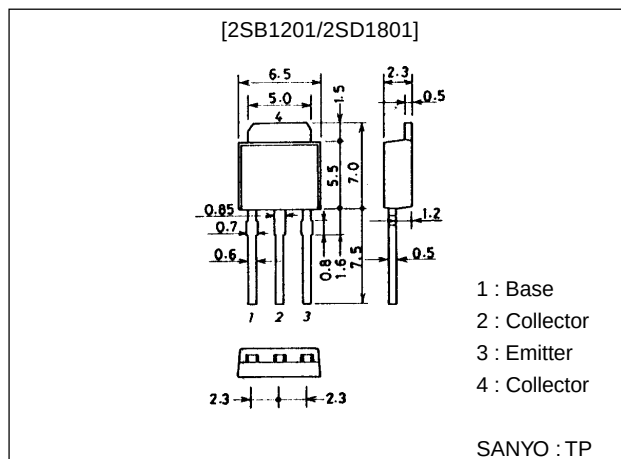
Features

- Adoption of FBET, MBIT processes.
- Large current capacity and wide ASO.
- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Small and slim package making it easy to make 2SB1201/2SD1801-used sets smaller.

Package Dimensions

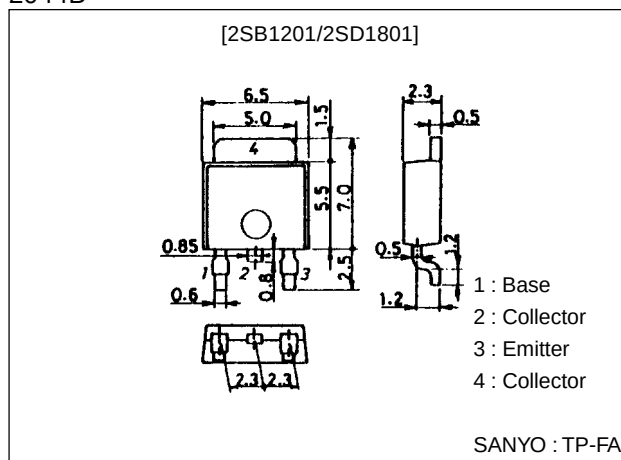
unit:mm

2045B



unit:mm

2044B



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92098HA (KT)/8259MO/4137KI/4076KI, TS No.2112-1/5

() : 2SB1201

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)50	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)2	A
Collector Current (Pulse)	I_{CP}		(-)4	A
Collector Dissipation	P_C		0.8	W
		Tc=25°C	15	W
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

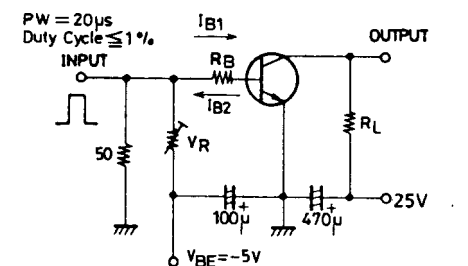
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)50V, I_E=0$			(-)100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0$			(-)100	nA
DC Current Gain	h_{FE1}	$V_{CE}=(-)2V, I_C=(-)100mA$	100*		560*	
	h_{FE2}	$V_{CE}=(-)2V, I_C=(-)1.5A$	40			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)50mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(22)12		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		0.15	0.4	V
				(-0.3)	(-0.7)	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-)0.9	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit		60		ns
Storage Time	t_{stg}	See specified Test Circuit		(450)		ns
				550		ns
Fall Time	t_f	See specified Test Circuit		30		ns

* : The 2SB1201/2SD1801 are classified by 100mA h_{FE} as follows :

100	R	200	140	S	280	200	T	400	280	U	560
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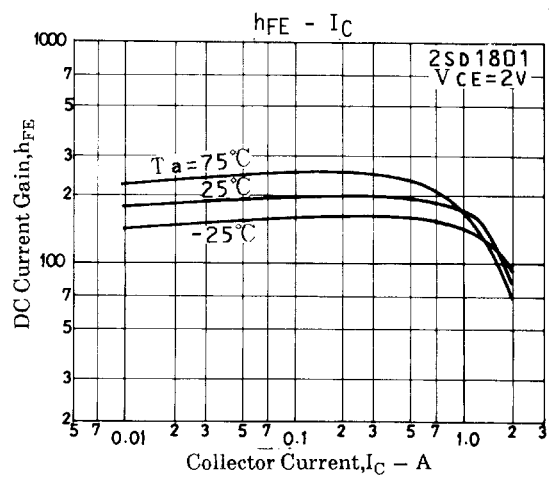
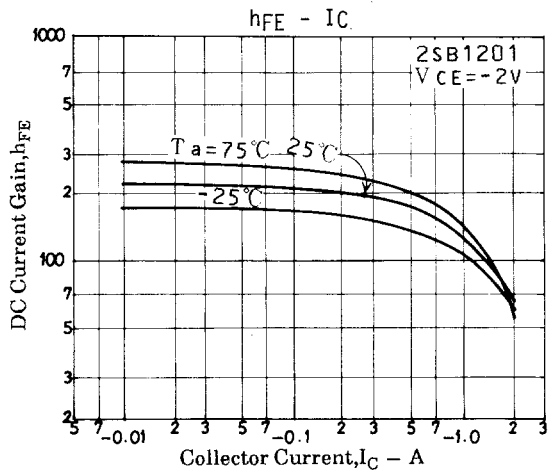
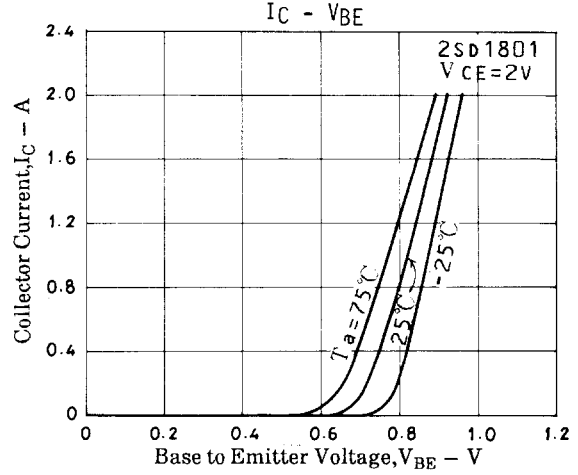
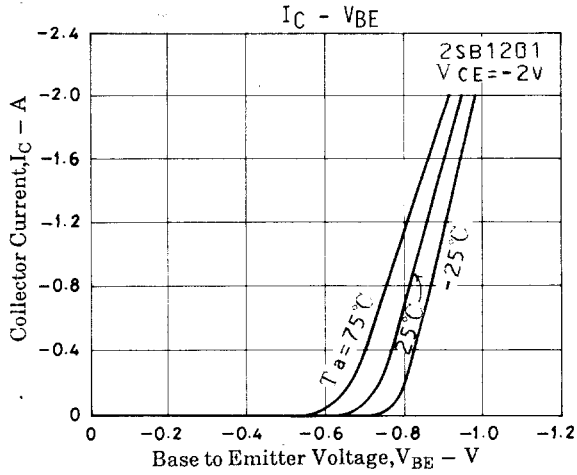
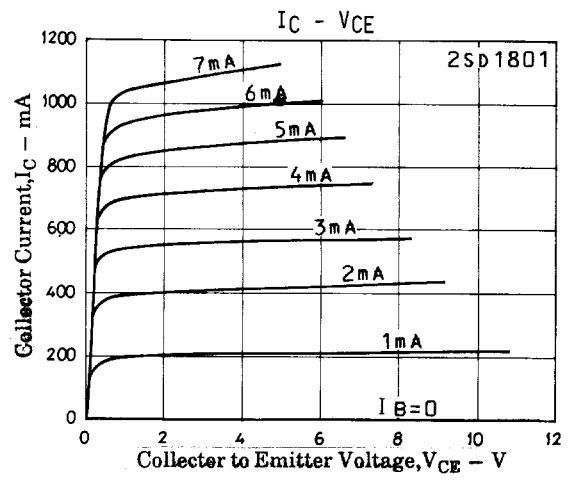
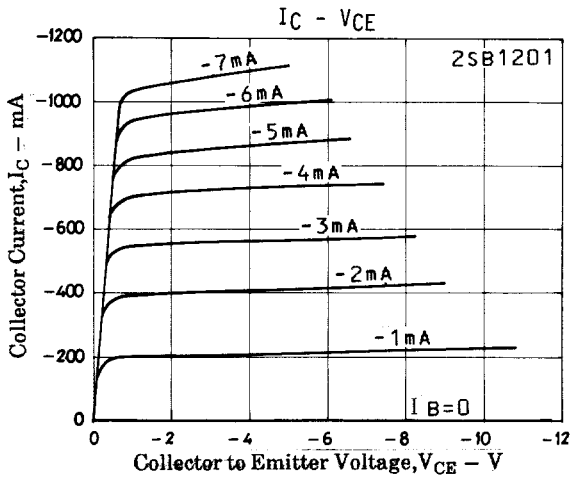
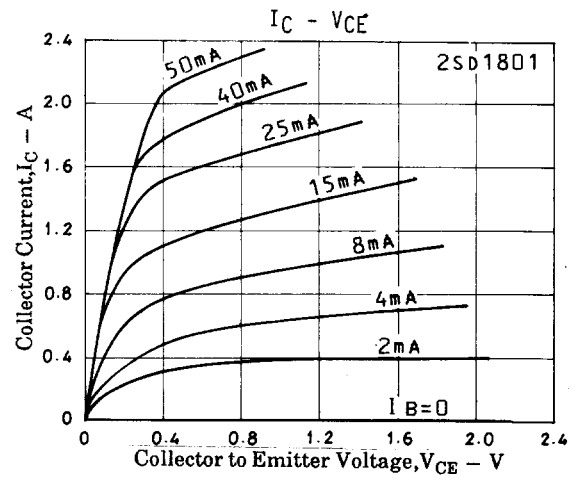
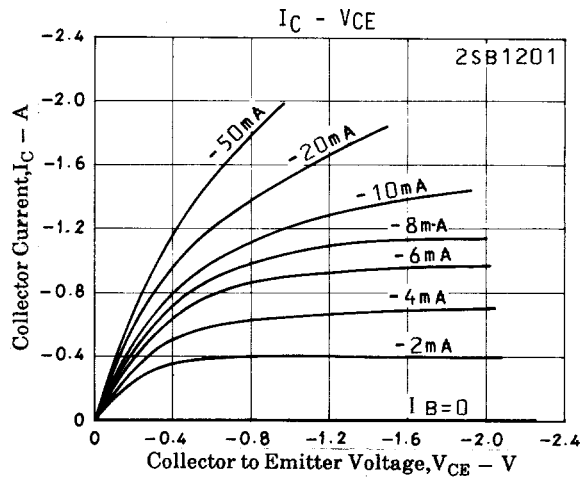
Switching Time Test Circuit



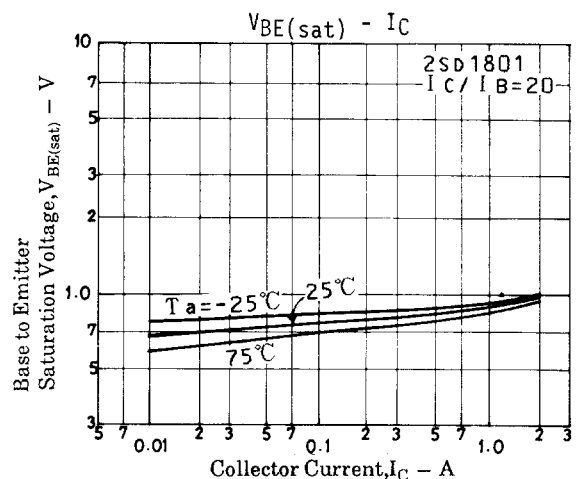
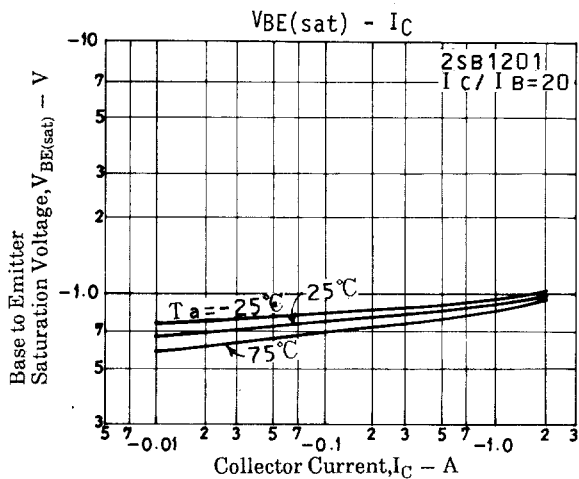
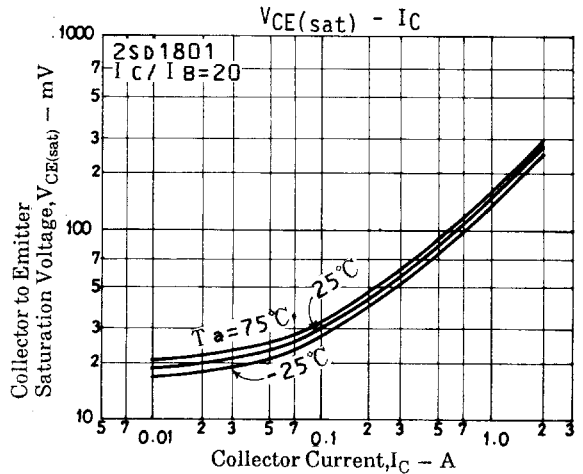
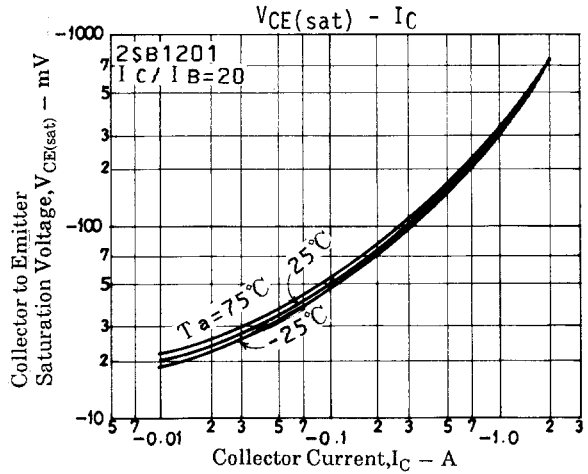
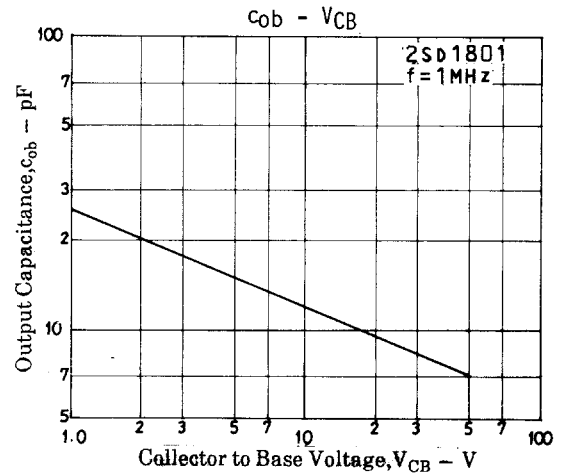
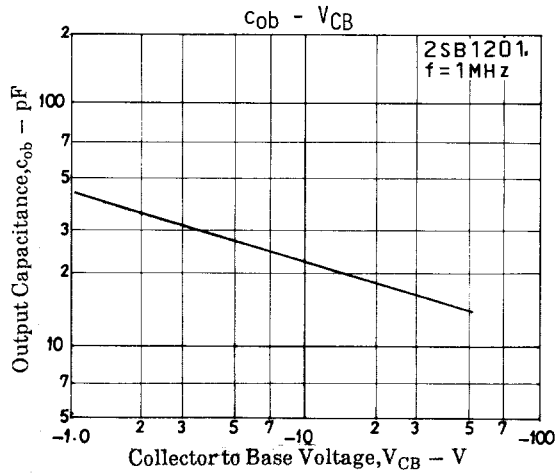
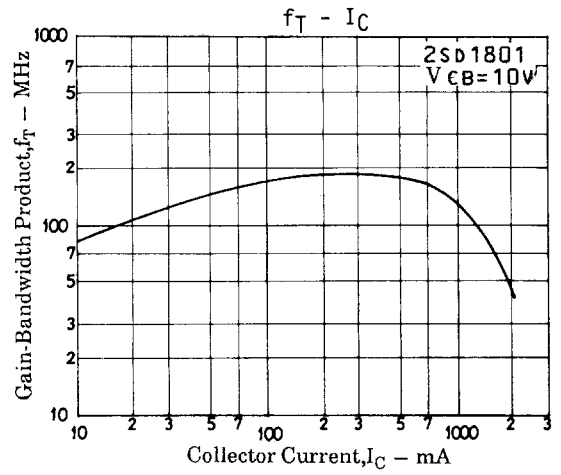
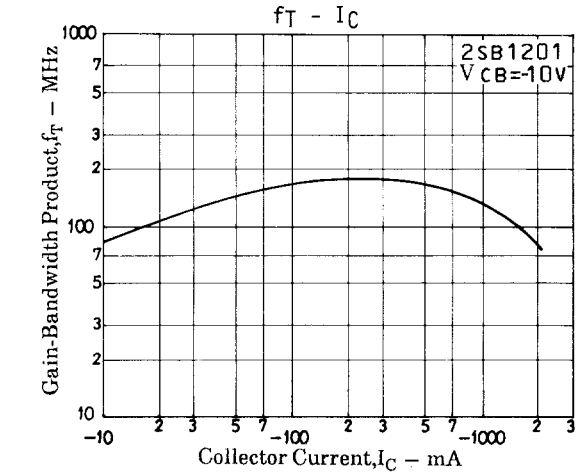
$I_C = 10 I_B$ $I_B = -10 I_{B2} = 500mA, V_{CC} = 25V$
(For PNP, the polarity is reversed.)

Unit (resistance : Ω , capacitance : F)

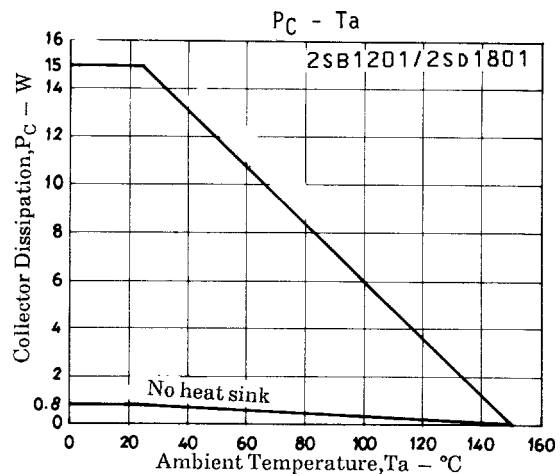
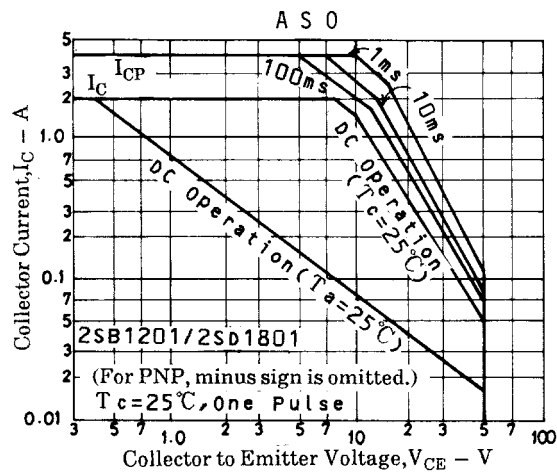
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